

### Simulations for Modeling of <u>Resonant Tunneling Diodes (RTDs)</u>

# Why:

- Tera-Hertz Devices possible, High Speed Analog Circuits
- III-V Semiconductors, useful in OptoElectronic Integrated Circuits (OEICS) – Increase electrical gain

## Modeling:

- Double Barrier acts as an electron supply followed by band-pass filter
- Appropriate potential model used is <u>Quantum Charge Self-Consistency</u>

## Problems:

- •Full Quantum Mechanical understanding needed
- Computation capacity restricts accuracy (especially 3D transport)



## **Results:**

- Results match with theoretical insights providing us with appropriate <u>Operational Limitations</u>
- Modeling Realistically extended systems remains a challenge, reduction in simulation time needed

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